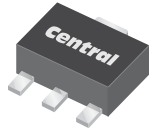


CXT853

**SURFACE MOUNT
HIGH CURRENT
NPN SILICON TRANSISTOR**



SOT-89 CASE



www.centralemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CXT853 type is a high current, high voltage silicon NPN transistor. Packaged in the SOT-89 surface mount case, the CXT853 is ideal for industrial and consumer applications requiring high energy efficiency in a small package.

MARKING: FULL PART NUMBER

FEATURES:

- Low Saturation Voltage:
 $V_{CE(SAT)}=0.340V \text{ MAX @ } I_C=5.0A$
- PNP Complement: CXT953

APPLICATIONS:

- Power Management
- Motor Driving
- DC/DC Converters
- Switching

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO}	200
V_{CEO}	100
V_{EBO}	6.0
I_C	6.0
P_D	1.2
T_J, T_{stg}	-65 to +150
Θ_{JA}	104

UNITS

V
V
V
A
W
$^\circ\text{C}$
$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=150V$			10	nA
I_{CBO}	$V_{CB}=150V, T_A=100^\circ\text{C}$			1.0	μA
I_{CER}	$V_{CE}=150V, R_{BE}\leq 1.0k\Omega$			10	nA
I_{EBO}	$V_{EB}=6.0V$			10	nA
BV_{CBO}	$I_C=100\mu\text{A}$	200	220		V
BV_{CER}	$I_C=10\text{mA}, R_{BE}\leq 1.0k\Omega$	200	210		V
BV_{CEO}	$I_C=10\text{mA}$	100	110		V
BV_{EBO}	$I_E=100\mu\text{A}$	6.0	8.0		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=5\text{mA}$		22	50	mV
$V_{CE(SAT)}$	$I_C=2.0A, I_B=100\text{mA}$		135	170	mV
$V_{CE(SAT)}$	$I_C=5.0A, I_B=500\text{mA}$			340	mV
$V_{BE(SAT)}$	$I_C=5.0A, I_B=500\text{mA}$			1.25	V

R1 (23-February 2010)

CXT853

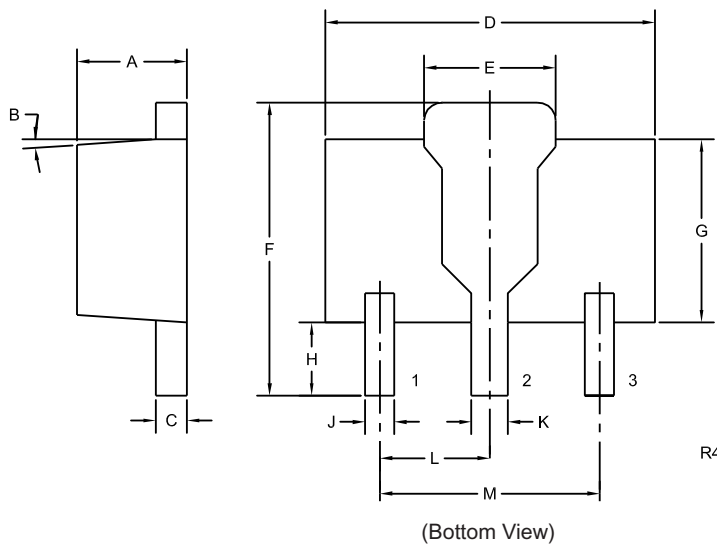
**SURFACE MOUNT
HIGH CURRENT
NPN SILICON TRANSISTOR**



ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
h_{FE}	$V_{CE}=2.0\text{V}$, $I_C=10\text{mA}$	100			
h_{FE}	$V_{CE}=2.0\text{V}$, $I_C=2.0\text{A}$	100	200	300	
h_{FE}	$V_{CE}=2.0\text{V}$, $I_C=4.0\text{A}$	50	100		
h_{FE}	$V_{CE}=2.0\text{V}$, $I_C=10\text{A}$	20	30		
f_T	$V_{CE}=10\text{V}$, $I_C=100\text{mA}$, $f=50\text{MHz}$		190		MHz
C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1.0\text{MHz}$		38		pF

SOT-89 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.014	0.018	0.35	0.46
D	0.173	0.185	4.40	4.70
E	0.064	0.074	1.62	1.87
F	0.146	0.177	3.70	4.50
G	0.090	0.106	2.29	2.70
H	0.028	0.051	0.70	1.30
J	0.014	0.019	0.36	0.48
K	0.017	0.023	0.44	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R4)

LEAD CODE:

- 1) Emitter
- 2) Collector
- 3) Base

MARKING:

FULL PART NUMBER

R1 (23-February 2010)